





EH25 00

Series —
RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm
Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±100ppm Maximum

Operating Temperature Range – 0°C to +70°C

TS -48.000M

Nominal Frequency 48.000MHz

Pin 1 Connection
Tri-State (High Impedance)

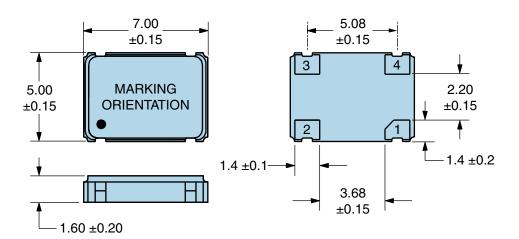
Duty Cycle 50 ±10(%)

Frequency Tolerance/Stability ±100 Ope Shoot Aging at 25°C ±5pp Operating Temperature Range 5.0V Supply Voltage nput Current 50m Output Voltage Logic High (Voh) Output Voltage Logic Low (Vol) 0.4V	.000MHz 00ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the perating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C,	
Open Shoot Shoot Shoot Shoot Shoot Shoot Shoot Shoot Shoot Supply Voltage Some Shoot Supply Voltage Some Some Some Some Some Some Some Som		
Operating Temperature Range 0°C Supply Voltage 5.0V nput Current 50m Output Voltage Logic High (Voh) 2.4V Output Voltage Logic Low (Vol) 0.4V	±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over to Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Supply Voltage 5.0V nput Current 50m Dutput Voltage Logic High (Voh) 2.4V Dutput Voltage Logic Low (Vol) 0.4V	ppm/year Maximum	
nput Current 50m Output Voltage Logic High (Voh) 2.4V Output Voltage Logic Low (Vol) 0.4V	0°C to +70°C	
Output Voltage Logic High (Voh) 2.4V Output Voltage Logic Low (Vol) 0.4V	0Vdc ±10%	
Output Voltage Logic Low (Vol) 0.4V	mA Maximum (No Load)	
	Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)	
Rise/Fall Time 6nSe	Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)	
	Sec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform the HCMOS Load)	
Outy Cycle 50 ±	±10(%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load)	
Load Drive Capability 10T	TTL Load or 50pF HCMOS Load Maximum	
Output Logic Type CMC	NOS	
Pin 1 Connection Tri-S	-State (High Impedance)	
	.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to able output.	
Absolute Clock Jitter ±250	50pSec Maximum, ±100pSec Typical	
One Sigma Clock Period Jitter ±50p	0pSec Maximum, ±30pSec Typical	
Start Up Time 10m	mSec Maximum	
Storage Temperature Range -55°	mood maximum	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	48.000M
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1



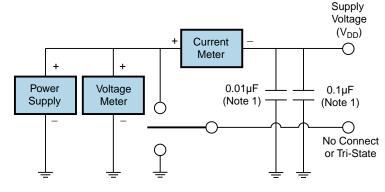
OUTPUT WAVEFORM & TIMING DIAGRAM

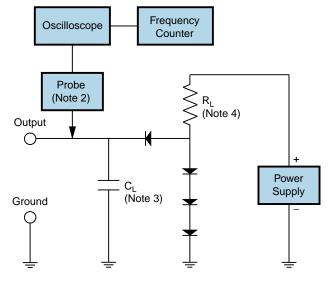


Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability





Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

3°C/second Maximum
150°C
175°C
200°C
60 - 180 Seconds
3°C/second Maximum
217°C
60 - 150 Seconds
260°C Maximum for 10 Seconds Maximum
250°C +0/-5°C
20 - 40 seconds
6°C/second Maximum
8 minutes Maximum
Level 1
Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)